EE105 - Spring 2001 - Homework 3 solutions 3.1) Jaiff = Jaiff = 9 Dn gr In = KT => Dn = unkT => Jdiff= q(unkT) dn Jdiff = qun Van (Nd(x=1)-Nd(x=0)) Jdiff= 1.6×10-19Cx 1400 cm2 x 0.026 V ( 10-4 cm3-10/2m3 Jdiff = 58.24 Az/ Jdr(x) = Jdr(x) = qn(x)un E Jn (x=0.5mm) = qn (x=0.5mm) un E = Jdiff  $E = 52 \, \text{kWm} \qquad \text{linearly doped implies n(0.5um)=[n(1um)-n(0)]/2 ~ 5e14} \\ \text{n(0.5um) != 5e12} \\ \text{Therefore the answer to part b should be -520V/cm}$ J(x) = Jdiff + Jdr(x) = Jdiff + 9n(x)-un E J(0) = 58,24 + 1.6x10-19Cx101/2m3x 1400cm2x 52x103V  $J(0) = 58,36 \frac{A}{cm^2}$  carrying down the value from part b...  $J(0)=58.239 \text{A/cm}^2$ J(x=14m) = 58,24 == +1.6x10-19C x101/2m3x1400cm2x52x103V carrying down the value from part b. (x=lum) = 11.7/x103 A/cm2 (d)  $J(1um) = -58.24A/cm^2$ 

3,2) 
$$E_{\text{max}} = \frac{-Q N d \times n}{E_{\text{S}}} = \frac{-Q N a \times p}{E_{\text{S}}}$$
 $X_{n} = \frac{-E_{\text{max}} E_{\text{S}}}{Q N d}$ 
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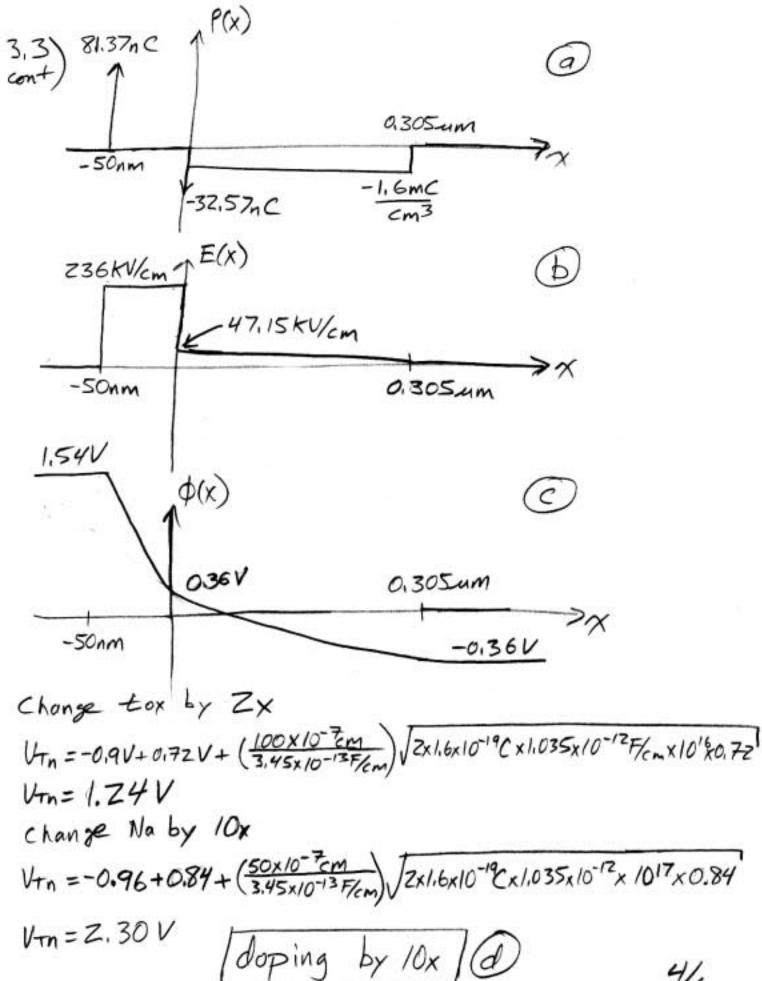
3,3) 
$$V_{Tn} = V_{FB} - Z\phi_P + \left(\frac{t_{ox}}{\epsilon_{ox}}\right)\sqrt{2g\epsilon_S}N_q(-2\phi_P)^{-7}$$

$$V_{FB} = -(\phi_n - \phi_P) = -\left(540mV - -360mV\right) = -0.9V$$

$$Z\phi_P = (z)(-360mV) = -0.72V$$

$$V_{Tn} = 0.528V$$
 $V_{GB} > V_{Tn} => inversion$ 

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4/6

5/6

(ent) Ndoped region and substrate form a Pn junction which has a copacitance. 2x1.035x10-12 F/cm x (-0.72V--5V) phi B is a positive number so -0.72 should not have a negative sign. Xd= 2,36um Xd=2.73um note that since the substrate is doped 100 times lighter than the n-region so 99% of this depletion region is in the substrate, and thus the n-region is not completely depleted. Carrying down Xd Cactive=3.79nF/cm^2 Cactive unit = 1.035x10-12F/cm = 4.39nF/cm2 Cactive total = 62 mm2 x 4.39 x 10-9 F/cm2 Carrying down again... CactiveTotal=2.35fF plus 32 mm² for "side walls"